

1. Product Name

Photo diode chip DS3-16

2. Absolute Maximum Ratings

Ta=25°C

Parameter	Symbol	Rating	Unit.
Reverse voltage	VR	15	V

3. Electro-Optical Characteristics

Ta=25°C

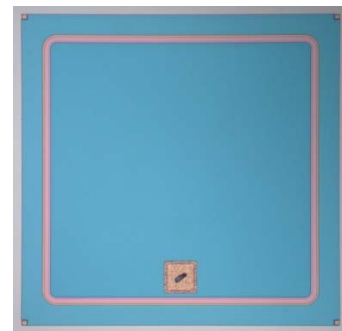
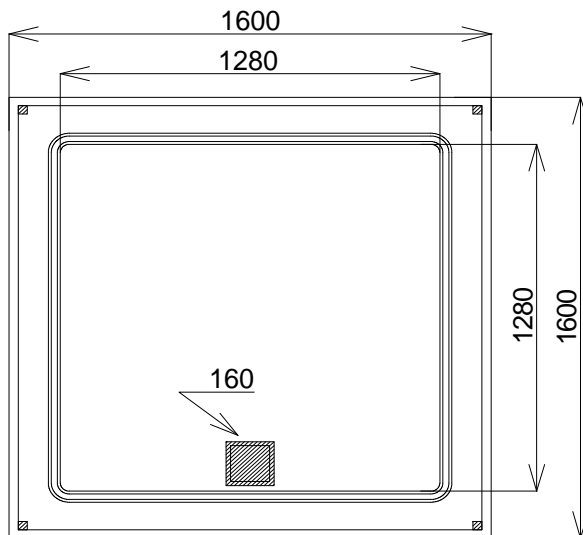
Parameter	Symbol	Condition	Min	Typ	Max	Unit.
Dark current	Id	VR=10V			20	nA
Spectral sensitivity	λ		450 ~ 1050			nm
Peak sensitivity wavelength	λp			920		nm
Terminal capacitance	Ct	VR=5V f=1MHz		5		pF

4. Dimension (Unit: μm)

Chip size ※1	□1600 μm
Chip thickness	400 ± 15 μm
Active area	□1280 μm

※1 The size after the dicing is □1560 μm .

Passivation	SiN
Fore side electrode	〈Anode〉Al
Back side electrode	〈Cathode〉Au
Wafer size	6inch



The contents of this data sheet are subject to change without advance notice for the purpose of improvement. When using this product, would you please refer to the latest specifications.